

M626x Series 5x7 mm, TCXO/TCVCXO

FEATURES APPLICATIONS

Frequencies from 10 MHz to 52 MHz Supports both TCXO and VCTCXO formats Tight stability ±0.1ppm over -40°C to +85°C Available in 4/5 pad and 10 pad configurations 3.0 V and 3.3 V versions Low phase noise performance Low G-sensitivity (0.6 ppb/G) version available Telecom / Datacom Industrial Controls Communications & Navigation

ORDERING INFORMATION

	M626x	2	J	F	С	Т
Product Series						
M6261 = 3.3 V						
M6262 = 3.0 V						
M6264 = 3.3 V Low 0						
M6265 = 3.0 V Low 0	3					
Temperature Rang	je					
1 : 0°C to +70°C	3 : -55°C t	:o +105°C				
6 : -20°C to +70°C	4 : -55°C	:o +125°C				
2 : -40°C to +85°C						
Stability						
L: ± 4.6 ppm	J : ± 1.0 ppm	M : ± 0	.20 ppm			
H : ± 2.5 ppm	G : ± 0.5 ppm	Q : ± 0.	.14 ppm			
(: ± 2.0 ppm	P : ± 0.3 ppm	N : ± 0.	.10 ppm			
Output Type						
T: Voltage Control W						
F: No Voltage Contro						
Output Waveform						
C: CMOS						
S: Clipped Sine Way						
Lead/Package Cor N: 10 Pad Leadless (_	T : 1/5 Da	ad Leadless C	`eramic		
IN. TO Pau Leauless (Jerannic	1.4/3 Pa	au Leauless C	-ciaiiiic		

Example Part Number: M62612JFCN 10.0000 MHz



ELECTRICAL SPECIFICATIONS

Parameter	Symbol	Min.	Тур.	Max.	Units	Conditions	
Frequency Range	F ₀	10		52	MHz		
Frequency Stabilities							
Initial Accuracy		-1.0		+1.0	ppm	@ +25°C	
vs. Operating	∆F/F	See ordering information		ppm	(FMAX-FMIN)/2 ¹		
Temperature	Δι / Ι					` ,	
vs. Reflow		-1	. 0. 00	+1	ppm	2 reflows max	
vs. Supply Voltage			±0.02	±0.1	ppm	5% voltage variation	
vs. Load		4.0	±0.02	±0.1	ppm	5% load variation	
vs. Aging (First Year)		-1.0		+1.0	10.10.00	F ₀ ≤ 20 MHz ²	
vs. Aging (First Year)		-2.0		+2.0	ppm	F ₀ > 20 MHz	
vs. Aging (10 Year)		-3.0 5.0		+3.0	ppm	F ₀ ≤ 20 MHz	
vs. Aging (10 Year)		-5.0	DE Oute	+5.0		F ₀ > 20 MHz	
			RF Outp		0/11		
Output Logic Level	Vol	00		20	%Vcc	IoL = +4mA, Vs = +3.0 V	
(CMOS)	Vон	80			%Vcc	I _{OH} = -4mA, Vs = +3.0 V	
Output Logic Level (Clipped Sinewave)	0.8				V _{pk-pk}		
Waveform Symmetry (duty cycle)	T _{DC}	40	50	60	%	@ 50% of waveform (CMOS)	
Rise/Fall Time	T _R /T _F			6.5	ns	CMOS	
Output Load			15		pF	CMOS ³	
Output Load			10/10		kΩ/pF	Clipped Sinewave Output ³	
Triatata Francisco		80% or Open			%V _{CC}	Output Enabled	
Tristate Function		·		20	%V _{CC}	Output Disabled: to HIGH Impedance (Z)	
Tristate Leakage Current		-100		+100	μΑ		
Input Leakage Current		-50		+50	μΑ		
Start-up Time	T _{SU}			10	ms		
		Frequ	ency Adj	ustment			
Control Voltage Bange	Vc	0.3		2.7	V	@ 3.0 V supply	
Control Voltage Range	VC	0.3		3.0	V	@ 3.3 V supply	
Tuning Range		±5.0			ppm	VCTCXO only ⁴	
Linearity				5	%		
Modulation Bandwidth		2			kHz		
Input Resistance		100			kΩ		
	Phase Noise						
			-98		dBc/Hz	@ 10Hz Offset	
SSB Phase Noise			-127		dBc/Hz	@ 100Hz Offset	
(measured @ 26 MHz)			-148		dBc/Hz	@ 1kHz Offset	
,			-156		dBc/Hz	@ 10kHz Offset	

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ELECTRICAL SPECIFICATIONS

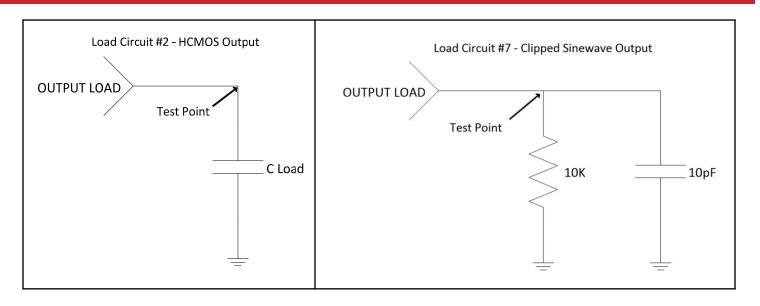
Operating Voltage and Current								
Parameter	Symbol	Min.	Тур.	Max.	Units	Conditions		
Operating Voltage	V _{CC}	3.135	3.300	3.465	V	M6261		
		2.850	3.000	3.150	V	M6262		
	I _C			4.4	mA	CMOS @ 16 MHz		
				5.5	mA	CMOS @ 26 MHz		
Operating Current				7.8	mA	CMOS @ 50 MHz		
Operating Current				3.5	mA	Clipped Sine @ 16 MHz		
				3.9	mA	Clipped Sine @ 26 MHz		
				5.0	mA	Clipped Sine @ 50 MHz		
	Temperature							
Operating Temperature	TA	See ordering information		°C				
Storage Temperature	Ts	-55		+125	°C			
Notes								
Note 1	Contact factory for less than ±1 ppm frequency stability.							
Note 2	Contact factory for less than ±1 ppm frequency aging.							
Note 3	Refer to the load circuit diagram in this data sheet.							
Note 4	Contact factory for other tuning range options.							

ENVIRONMENTAL SPECIFICATIONS/QUALIFICATION TESTING PERFORMED

Test	Test Method	Test Condition
Electrical Characteristics	Internal Specification	Per product specification
Frequency vs. Temperature	Internal Specification	Per product specification
Mechanical Shock	MIL-STD-202, Method 213, Condition C	100 g, 6 ms
Vibration	Per MIL-STD-202, Methods 201 & 204	10 g from 10-2000 Hz
Thermal Cycle	MIL-STD-883 TM 1010 Condition B	-55°C to +125°C, 15-minute Dwell, 100
Thermal Cycle	IVIIE-31B-003 TW TOTO CONDITION B	cycles
Accelerated Aging	MIL-PRF-3098	72 hours at 125°C
Gross Leak	MIL-STD-202, Method 112	30 Second Immersion (Crystal Only)
Fine Leak	MIL-STD-202, Method 112	Must meet 1x10-8 (Crystal Only)
Solderability	J-STD-002 Cond C, Test S1	8 Hour Steam Age – Must Exhibit 95%
Solderability	J-51D-002 Colld C, Test 51	coverage
Resistance to Solvents	MIL-STD-883, Method 2015	Three 1-minute soaks
Physical Dimensions	MIL-STD-883, Method 2016	Per Specification
Internal Visual	Internal Specification	Per Internal Specification

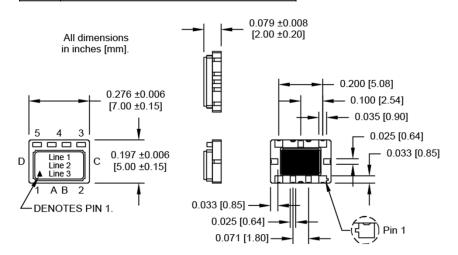


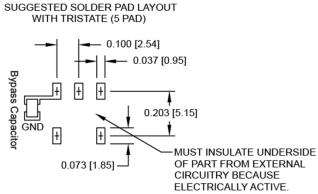
LOAD CIRCUIT DIAGRAMS



MECHANICAL AND PIN OUT INFORMATION - Package Code T (4/5 Pad)

Pad	Function
1	Voltage Control or N/C
Α	N/C – Do Not Connect
В	N/C – Do Not Connect
2	Ground
С	N/C – Do Not Connect
3	Output
4	Tristate or N/C - Do Not Connect
5	Supply Vcc+
D	N/C – Do Not Connect

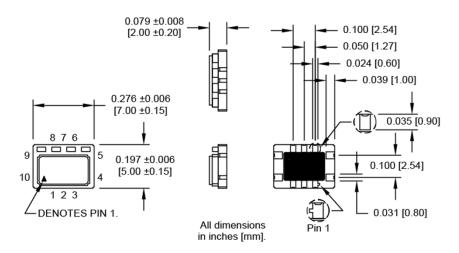


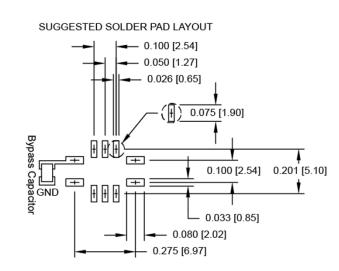




MECHANICAL AND PIN OUT INFORMATION - Package Code N (10 Pad)

Pad	Function
1	N/C – Do Not Connect
2	N/C – Do Not Connect
3	N/C – Do Not Connect
4	Ground
5	Output
6	N/C – Do Not Connect
7	N/C – Do Not Connect
8	Tristate or N/C - Do Not Connect
9	Supply Vcc+
10	Voltage Control or N/C





HANDLING INFORMATION

Although protection circuitry has been designed into the M626x oscillator, proper precautions should be taken to avoid exposure to electrostatic discharge (ESD) during handling and mounting.

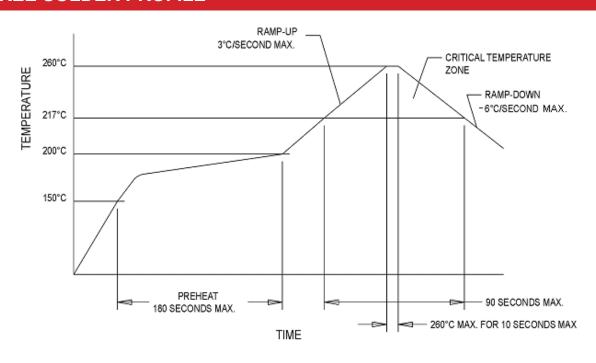
Model	ESD Threshold, Minimum	Unit
Human Body	≥ 2000*	V
Latch Up	≥ 200*	V

*JEITA ED-4701/302 Method 306B

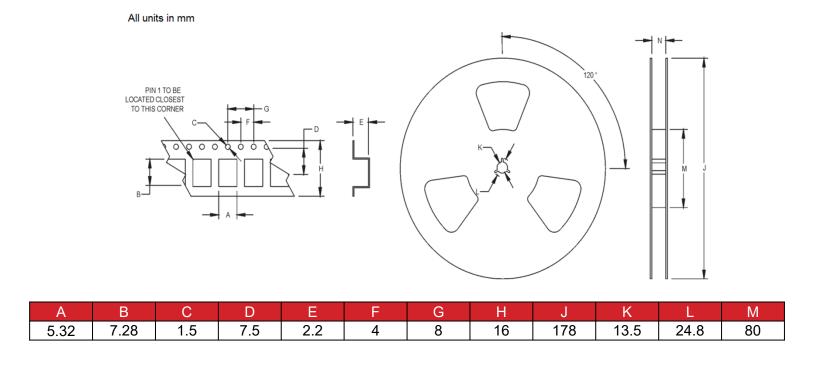




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TAPE AND REEL SPECIFICATIONS



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